

ABSTRACT OF THE DISCLOSURE

A method of manufacturing a semiconductor device includes a process for forming a photoresist pattern. In the disclosed process, residual photoresist polymers are removed using a photoresist polymer remover composition that

5 includes: (a) 5% to 15% of sulfuric acid based on the total weight of said composition, (b) 1% to 5% of hydrogen peroxide or 0.0001% to 0.05% of ozone based on the total weight of said composition, (c) 0.1% to 5% of acetic acid based on the total weight of said composition, (d) 0.0001% to 0.5% of ammonium fluoride based on the total weight of said composition and (e) remaining amount of water.